

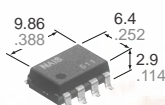
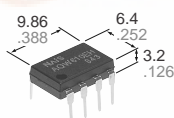


NAIS

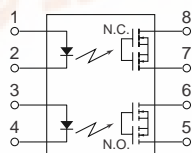
GU (General Use)-E Type 2-Channel (Form A Form B) Type

PhotoMOS RELAYS

FEATURES



mm inch



1. Reinforced insulation 5,000 V type
More than 0.4 mm internal insulation distance between inputs and outputs. Conforms to EN41003, EN60950 (reinforced insulation).

2. Compact 8-pin DIP size
The device comes in a compact (W) 6.4×(L)9.86×(H)3.2 mm (W).252×(L).388×(H).126 inch, 8-pin DIP size (through hole terminal type).

3. Applicable for 1 Form A 1 Form B use as well as two independent 1 Form A and 1 Form B use

4. Controls low-level analog signals
PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. High sensitivity, high speed response.
Can control a maximum 0.14 A load current with a 5 mA input current. Fast operation speed of 0.5ms (typ.) [N.O.].(AQW610EH)

6. Low-level off state leakage current

TYPICAL APPLICATIONS

- Modem
- Telephone equipment
- Security equipment
- Sensors

TYPES

Type	I/O isolation voltage	Output rating*		Part No.				Packing quantity	
				Through hole terminal	Surface-mount terminal		Tube	Tape and reel	
		Load voltage	Load current		Tube packing style				Tape and reel packing style
AC/DC type	Reinforced 5,000 V	350 V	120 mA	AQW610EH	AQW610EHA	AQW610EHAX	AQW610EHAZ	1 tube contains 40 pcs. 1 batch contains 400 pcs.	1,000 pcs.
		400 V	100 mA	AQW614EH	AQW614EHA	AQW614EHAX	AQW614EHAZ		

*Indicate the peak AC and DC values.

Note:

For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Symbol	AQW610EH (A)	AQW614EH (A)	Remarks
Input	LED forward current	I _F	50 mA		
	LED reverse voltage	V _R	3 V		
	Peak forward current	I _{FP}	1 A		f = 100 Hz, Duty factor = 0.1%
	Power dissipation	P _{in}	75 mW		
Output	Load voltage (peak AC)	V _L	350 V	400 V	
	Continuous load current	I _L	0.12 A (0.13 A)	0.1 A (0.13 A)	Peak AC, DC () : in case of using only 1a or 1b, 1 channel
	Peak load current	I _{peak}	0.36 A	0.3 A	100 ms (1 shot), V _L = DC
	Power dissipation	P _{out}	800 mW		
Total power dissipation		P _T	850 mW		
I/O isolation voltage		V _{iso}	5,000 V AC		
Temperature limits	Operating	T _{opr}	-40°C to +85°C -40°F to +185°F		Non-condensing at low temperatures
	Storage	T _{stg}	-40°C to +100°C -40°F to +212°F		



AQW610EH

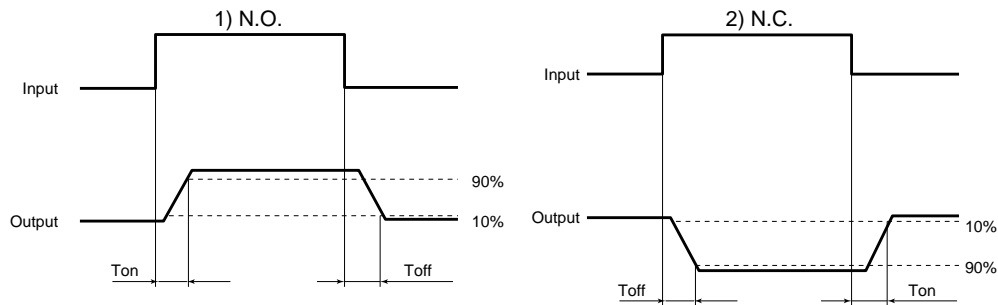
2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item		Symbol	AQW610EH (A)	AQW614EH (A)	Condition	
Input	LED operate current	Typical	1.3 mA		$I_L = \text{Max.}$	
		Maximum	3.0 mA			
	LED reverse current	Minimum	0.4 mA		$I_L = \text{Max.}$	
		Typical	1.2 mA			
LED dropout voltage	Typical	V_F	1.14 (1.25 V at $I_F = 50 \text{ mA}$)		$I_F = 5 \text{ mA}$	
	Maximum		1.5 V			
Output	On resistance	Typical	18Ω	26Ω	$I_F = 5 \text{ mA (N.O.)}$ $I_F = 0 \text{ mA (N.C.)}$ $I_L = \text{Max.}$ Within 1 s on time	
		Maximum	25Ω	35Ω		
	Off state leakage current	Maximum	I_{Leak}	1μA (N.O.) 10μA (N.C.)		$I_F = 0 \text{ mA (N.O.)}$ $I_F = 5 \text{ mA (N.C.)}$ $V_L = \text{Max.}$
Transfer characteristics	Operate (OFF) time*	Typical	$T_{on(N.O.)}$ 0.5 ms (N.O.) 1.0 ms (N.C.)	$T_{on(N.O.)}$ 0.5 ms (N.O.) 0.8 ms (N.C.)	$I_F = 0 \text{ mA} \rightarrow 5 \text{ mA}$ $I_L = \text{Max.}$	
		Maximum	3.0 ms			
	Reverse (ON) time*	Typical	$T_{off(N.O.)}$ 0.08ms (N.O.) 0.2ms (N.C.)			$I_F = 5 \text{ mA} \rightarrow 0 \text{ mA}$ $I_L = \text{Max.}$
		Maximum	1.0ms			
	I/O capacitance	Typical	C_{iso}	0.8 pF		$f = 1 \text{ MHz}$ $V_B = 0$
Maximum		1.5 pF				
Initial I/O isolation resistance	Minimum	R_{iso}	1,000MΩ		500 V DC	

Note: Recommendable LED forward current $I_F = 5$ to 10 mA.

For type of connection, see page 32.

*Operate/Reverse time



■ For Dimensions, see Page 27.

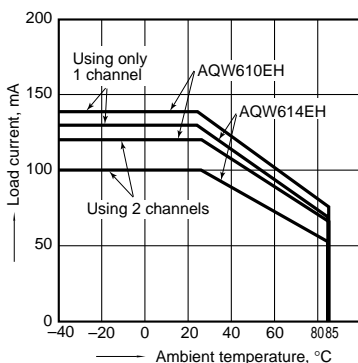
■ For Schematic and Wiring Diagrams, see Page 32.

■ For Cautions for Use, see Page 36.

REFERENCE DATA

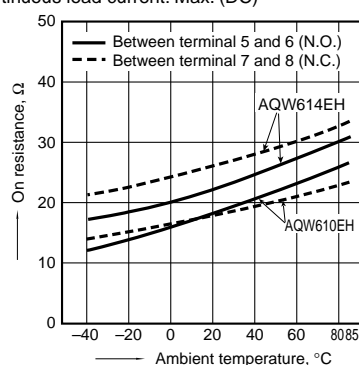
1. Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40°C to +85°C
-40°F to +185°F



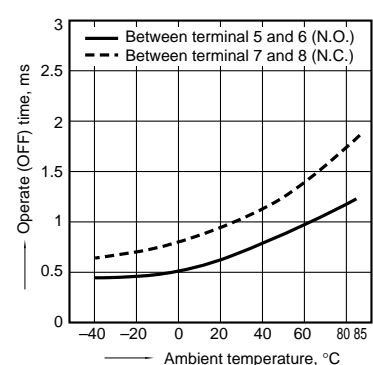
2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
LED current: 5 mA; Load voltage: Max. (DC)
Continuous load current: Max. (DC)



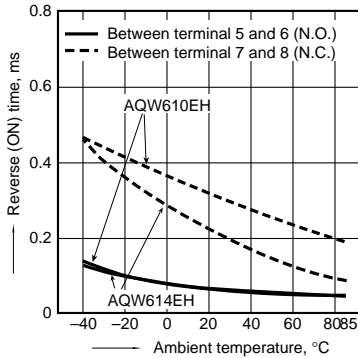
3. Operate time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



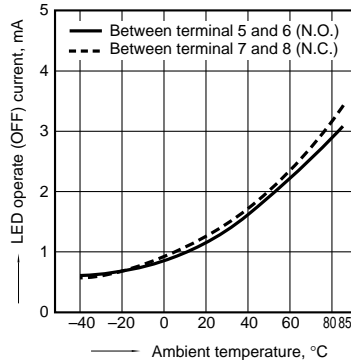
4. Reverse time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



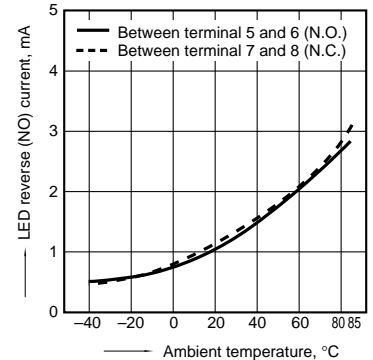
5. LED operate current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



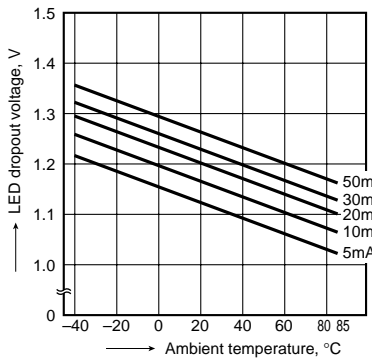
6. LED reverse current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



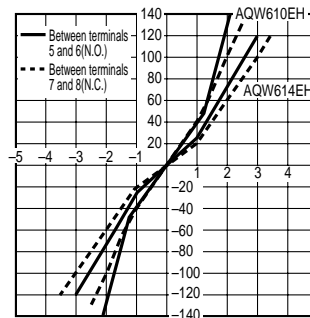
7. LED dropout voltage vs. ambient temperature characteristics

LED current: 5 to 50 mA



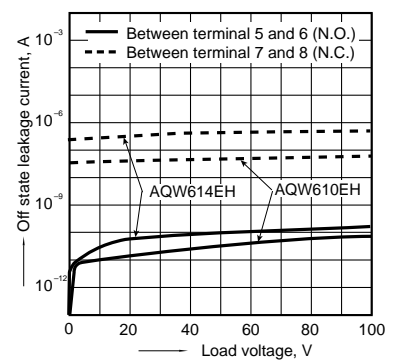
8. Voltage vs. current characteristics of output at MOS portion

Measured portion: between terminals 5 and 6, 7 and 8; Ambient temperature: 25°C 77°F



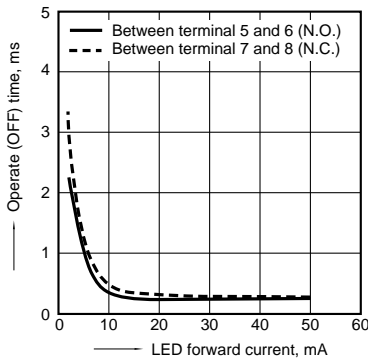
9. Off state leakage current

Measured portion: between terminals 5 and 6, 7 and 8; Ambient temperature: 25°C 77°F



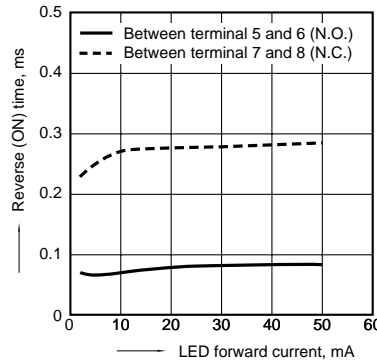
10. LED forward current vs. operate time characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



11. LED forward current vs. reverse (ON) time characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



12. Applied voltage vs. output capacitance characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Frequency: 1 MHz; Ambient temperature: 25°C 77°F

